

N-Channel 30 V (D-S) MOSFET with Schottky Diode

DESCRIPTION

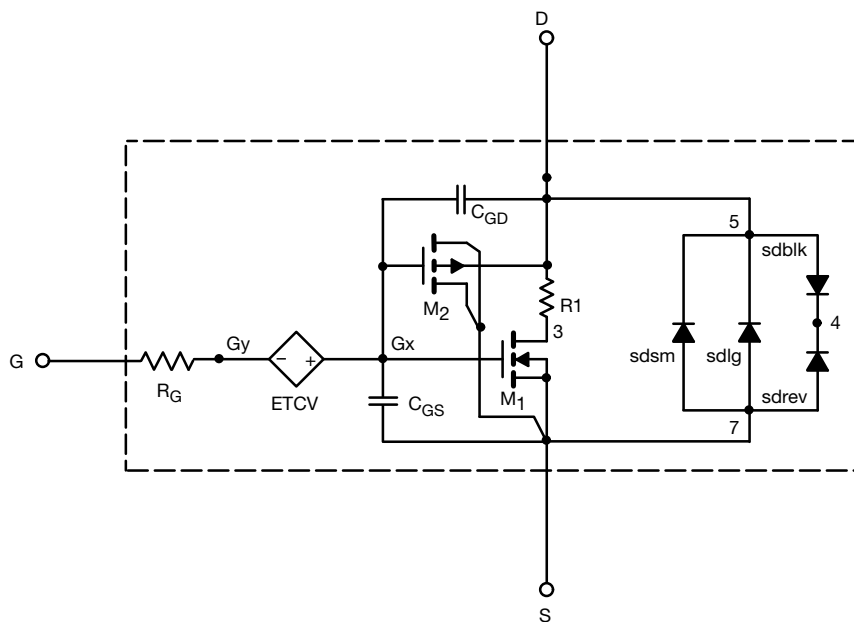
The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

CHARACTERISTICS

- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the - 55 °C to + 125 °C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

SUBCIRCUIT MODEL SCHEMATIC



Note

- This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



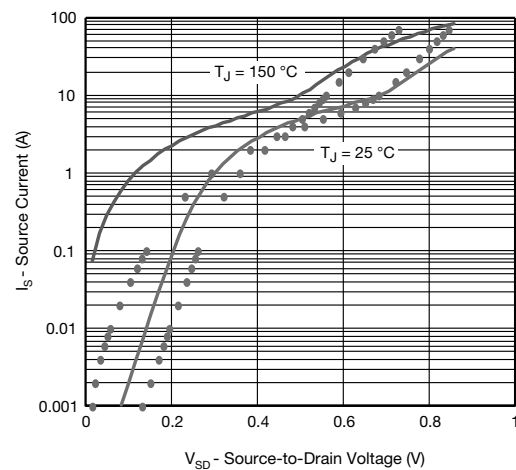
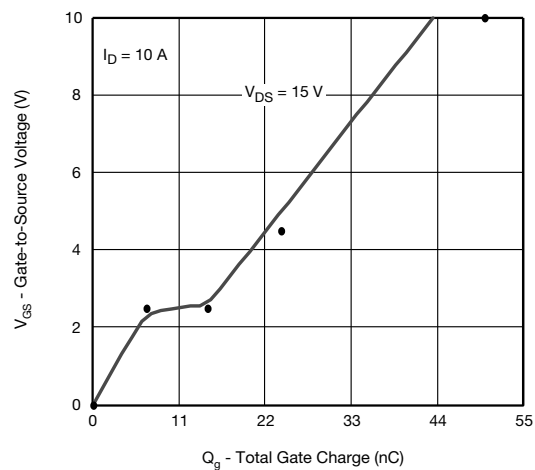
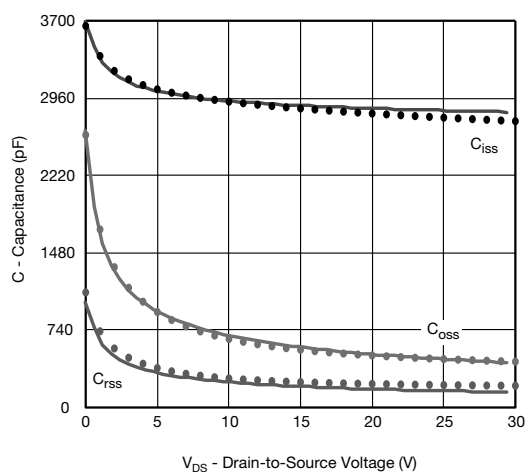
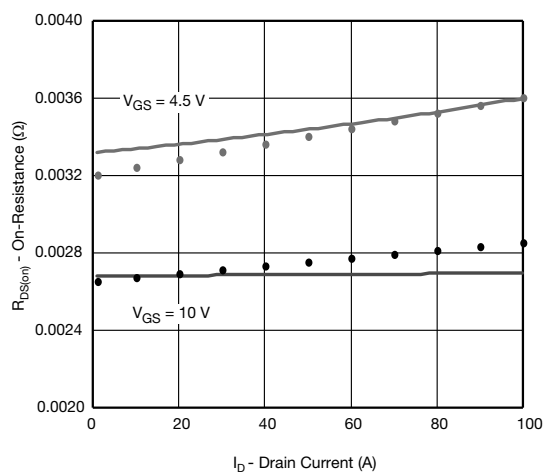
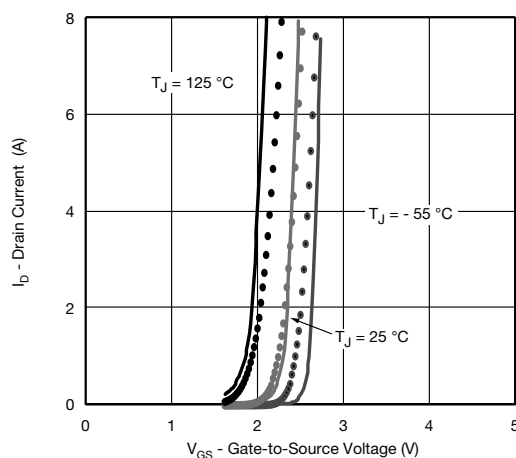
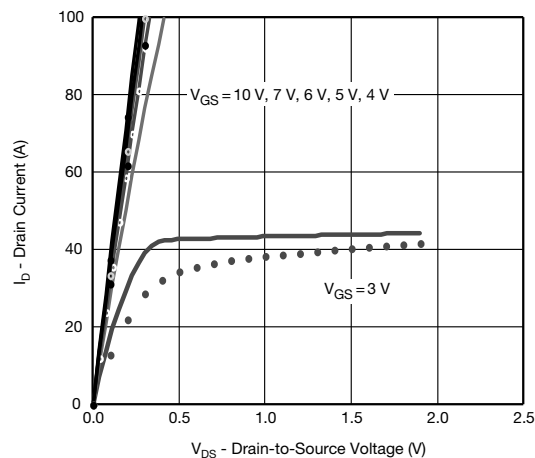
SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	1.6	-	V
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 20\text{ A}$	0.0027	0.0027	Ω
		$V_{GS} = 4.5\text{ V}$, $I_D = 10\text{ A}$	0.0033	0.0033	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}$, $I_D = 20\text{ A}$	79	85	S
Body Diode Voltage	V_{SD}	$I_S = 3\text{ A}$	0.42	0.47	V
Dynamic^b					
Input Capacitance	C_{iss}	$V_{DS} = 15\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$	2890	2873	pF
Output Capacitance	C_{oss}		578	555	
Reverse Transfer Capacitance	C_{rss}		209	246	
Total Gate Charge	Q_g	$V_{DS} = 15\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 10\text{ A}$	44	50	nC
Gate-Source Charge	Q_{gs}	$V_{DS} = 15\text{ V}$, $V_{GS} = 4.5\text{ V}$, $I_D = 10\text{ A}$	22	24	
Gate-Source Charge	Q_{gs}		6.8	6.8	
Gate-Drain Charge	Q_{gd}		7.8	7.8	

Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.



COMPARISON OF MODEL WITH MEASURED DATA ($T_J = 25^\circ\text{C}$, unless otherwise noted)



Note

- Dots and squares represent measured data.